

Surface Mount - 800V > BTA12-600BW3G, BTA12-800BW3G,

Maximum Ratings $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

Thyristors

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, T_J = -40° to 125°C) BTA12-600BW3G BTA12-800BW3G	V _{DRM} , V _{RRM}	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 80$ °C)	I _{T (RMS)}	12	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = 25°C)	I _{TSM}	105	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	46	A²sec
Non-Repetitive Surge Peak Off-State Voltage ($T_J = 25$ °C, $t = 10$ ms)	V _{DSM} /V _{RSM}	V _{DSM} /V _{RSM} +100	V
Peak Gate Current ($T_J = 125$ °C, t = 20ms)	I _{GM}	4.0	А
Peak Gate Power (Pulse Width \leq 1.0 μ s, T_{c} = 80°C)	P _{G(AV)}	20	W
Average Gate Power ($T_J = 125^{\circ}$ C)	P _{G(AV)}	1.0	W
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +125	°C
RMS Isolation Voltage (t = 300 ms, R.H. \leq 30%, T _A = 25°C)	V _{iso}	2500	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{8JC}	2.5 60	°C/W
Maximum Lead Temperature for Sold 10 seconds	ering Purposes, 1/8" from case for	T _L	260	°C

^{1.} V_{DRM} and V_{BRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



Surface Mount -800V > BTA12-600BW3G, BTA12-800BW3G,

Electrical Characteristics • **OFF** (T₁ = 25°C unless otherwise noted; Electricals apply in both directions)

Thyristors

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	$T_{_{\rm J}}=25^{\circ}{\rm C}$	I _{DRM} ,	-	-	0.005	
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_{_{\rm J}} = 125^{\circ}\text{C}$	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - ON (T_j = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Forward On-State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A Peak}$)	Forward On-State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A Peak}$)		_	_	1.55	V
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 30 \Omega$)	MT2(+), G(+)		2.5	-	50	
	MT2(+), G(-)	l _{GT}	2.5	-	50	mA
	MT2(-), G(-)		2.5	_	50	
Holding Current $(V_D = 12 \text{ V}, \text{ Gate Open, Initiating Current} = \pm 100 \text{ mA})$		IH	_	_	50	mA
	MT2(+), G(+)		_	_	70	
Latching Current ($V_D = 24 \text{ V}$, $I_G = 60 \text{ mA}$)	MT2(+), G(-)	IL	_	-	80	mA
	MT2(-), G(-)		_	_	70	
	MT2(+), G(+)		0.5	-	1.7	
Gate Trigger Voltage (V $_{\rm D}$ = 12 V, R $_{\rm L}$ = 30 $\Omega)$	MT2(+), G(-)	V _{GT}	0.5	_	1.1	V
	MT2(-), G(-)		0.5	-	1.1	
	MT2(+), G(+)		0.2	-	-	
Gate Non-Trigger Voltage (T _J = 125°C)	MT2(+), G(-)	t _{gt}	0.2	-	-	V
	MT2(-), G(-)		0.2	-	-	

^{2.} Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.



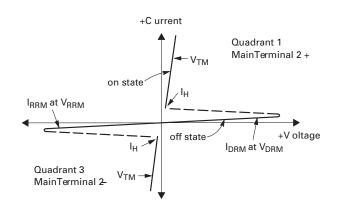
Dynamic Characteristics

Characteristic		Min	Тур	Max	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, T _J = 125°C, No Snubber)	(dl/dt)c	2.5	-	_	A/ms
Critical Rate of Rise of On–State Current ($T_J = 125$ °C, $f = 120$ Hz, $I_G = 2 \times I_{GT}$, $tr \le 100$ ns)	dl/dt	-	-	50	A/µs
Critical Rate of Rise of Off-State Voltage $(V_D = 0.66 \times V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)$		2000	-	-	V/µs

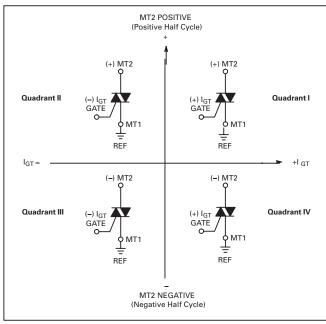
Voltage Current Characteristic of SCR

Symbol	Parameter		
V _{DRM}	Peak Repetitive Forward Off State Voltage		
I _{DRM}	Peak Forward Blocking Current		
V _{RRM}	Peak Repetitive Reverse Off State Voltage		
I _{RRM}	Peak Reverse Blocking Current		
V _{TM}	Maximum On State Voltage		
I _H	Holding Current		

Thyristors



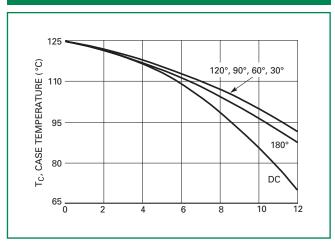
Quadrant Definitions for a Triac



All polarities are referenced to MT1. With in-phase signals (using standard AC lines) quadrants I and III are used

© 2017 Littelfuse, Inc. Specifications are subject to change without notice. Revised: 08/30/17

Figure 1. RMS Current Derating



Thyristors

Figure 2. On-State Power Dissipation

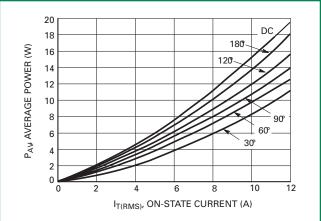


Figure 3. On-State Characteristics

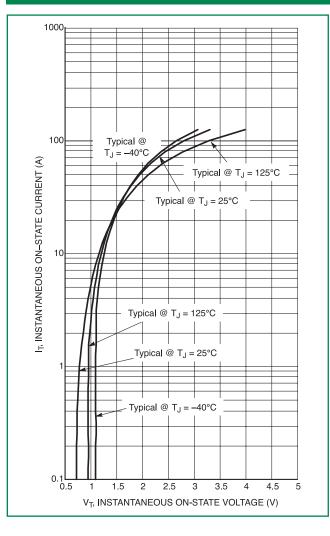


Figure 4. Thermal Response

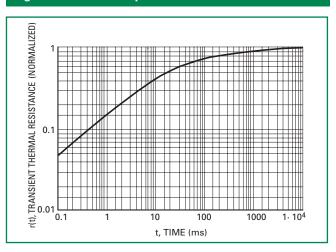
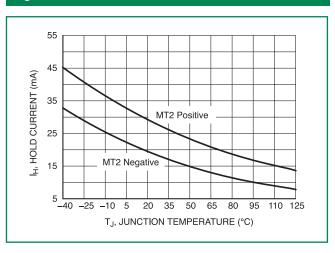
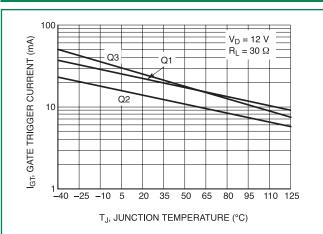


Figure 5. Hold Current Variation



Surface Mount - 800V > BTA12-600BW3G, BTA12-800BW3G,

Figure 6. Gate Trigger Current Variation



Thyristors

Figure 8. Critical Rate of Rise of Off-State Voltage

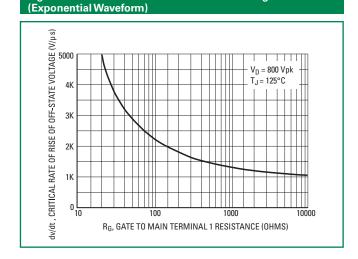


Figure 7. Gate Trigger Voltage Variation

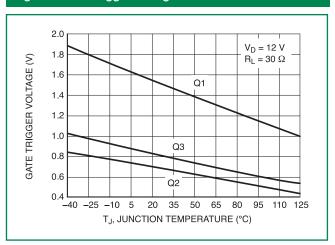
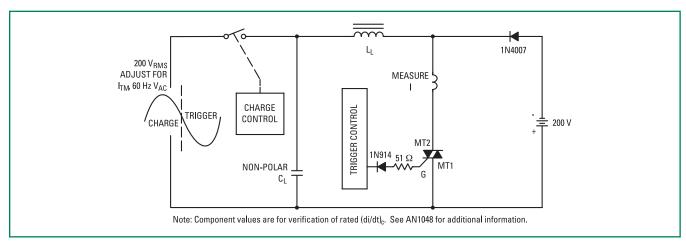


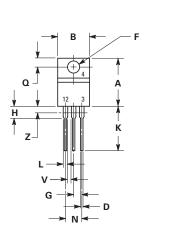
Figure 10. Latching Current Variation

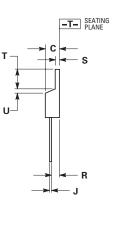
Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)



Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information

Dimensions

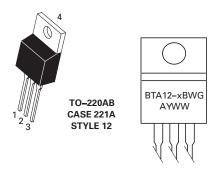




<u> </u>	Inches		Millim	neters	
Dim	Min	Max	Min	Max	
А	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.014	0.022	0.36	0.55	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

Part Marking System



x= 6 or 8 A= Assen

Assembly Location (Optional)*

 $\begin{array}{ll} Y = & Year \\ WW & = Work \ Week \\ G = & Pb - Free \ Package \end{array}$

* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

Pin Assignment	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	No Connection

Ordering Information

Device	Package	Shipping
BTA12-600BW3G	TO-220AB (Pb-Free)	50 Units / Rail
BTA12-800BW3G	TO-220AB (Pb-Free)	50 Units / Rail

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at: www.littelfuse.com/disclaimer-electronics.